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SS12 THRU SS1200

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 1.0 Ampere

产 品 规 格 书

承 认 书

客户确认：

公司签章：

部门	工程部	品保部	采购部
签名			
日期			

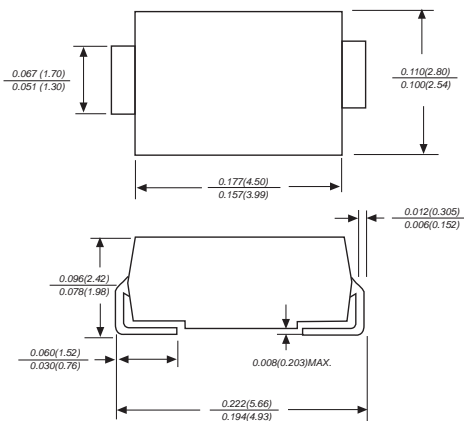


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DO-214AC/SMA



FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Metal silicon junction, majority carrier conduction
- ◆ Low power loss, high efficiency
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 250°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC DO-214AC molded plastic body
Terminals: leads solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.002 ounce, 0.07 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

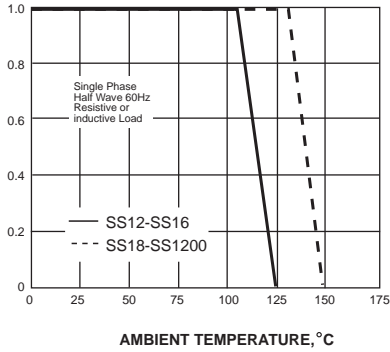
TYPE NUMBER	SYMBOLS	SS12	SS13	SS14	SS15	SS16	SS18	SS110	SS1150	SS1200	UNITS	
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	VOLTS	
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	VOLTS	
Maximum average forward rectified current at TL(see fig.1)	$I_{(AV)}$	1.0									Amp	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0									Amps	
Maximum instantaneous forward voltage at 1.0A	V_F	0.45	0.55	0.70			0.85		0.95		Volts	
Maximum DC reverse current at rated DC blocking voltage	I_R	0.5						0.2		mA		
Typical junction capacitance (NOTE 1)	C_J	110			90						pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	88.0									°C/W	
Operating junction temperature range	T_J	-50 to +125					-50 to +150					°C
Storage temperature range	T_{STG}	-50 to +150									°C	

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

SS12 THRU SS1200

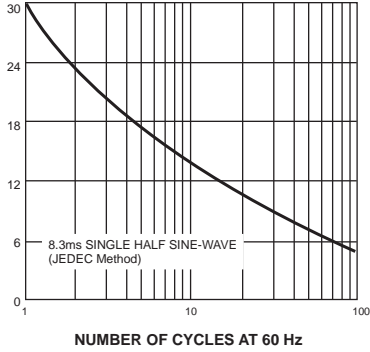
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



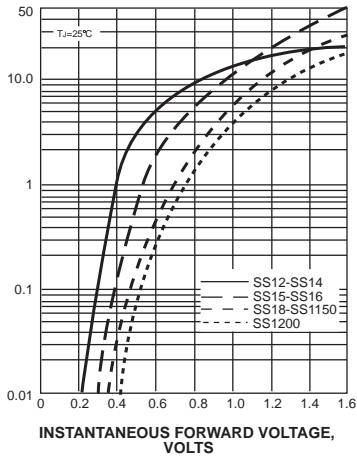
PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



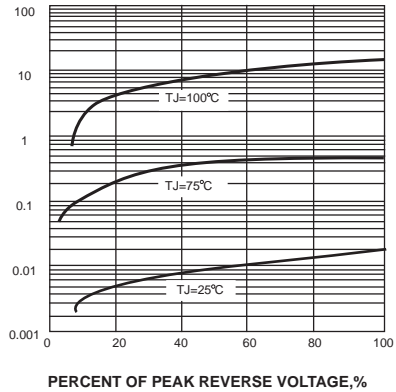
INSTANTANEOUS FORWARD CURRENT,AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



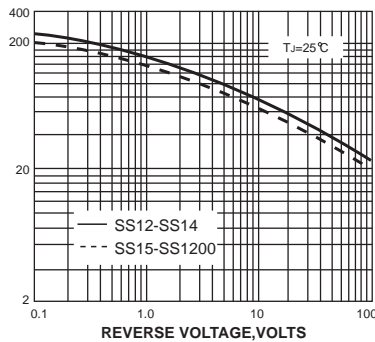
INSTANTANEOUS REVERSE CURRENT,
MILLIAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE,
°C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE

